

2SD2359

Silicon NPN epitaxial planer type

For low-frequency amplification

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

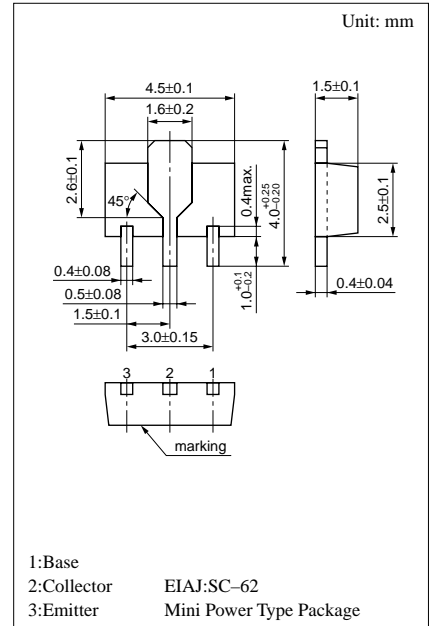
Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------|-----------|------------|------|
| Collector to base voltage | V_{CBO} | 20 | V |
| Collector to emitter voltage | V_{CEO} | 20 | V |
| Emitter to base voltage | V_{EBO} | 5 | V |
| Peak collector current | I_{CP} | 1.2 | A |
| Collector current | I_C | 1 | A |
| Collector power dissipation | P_C^* | 1 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 ~ +150 | °C |

* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

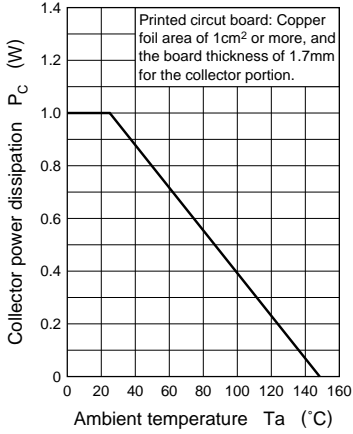
Electrical Characteristics (Ta=25°C)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---------------|--|-----|------|-----|------|
| Collector cutoff current | I_{CBO} | $V_{CB} = 14V, I_E = 0$ | | | 1 | μA |
| Collector to base voltage | V_{CBO} | $I_C = 10\mu A, I_E = 0$ | 20 | | | V |
| Collector to emitter voltage | V_{CEO} | $I_C = 1mA, I_B = 0$ | 20 | | | V |
| Emitter to base voltage | V_{EBO} | $I_E = 10\mu A, I_C = 0$ | 5 | | | V |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 2V, I_C = 100mA$ | 200 | | 800 | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 500mA, I_B = 10mA$ | | 0.11 | 0.2 | V |
| Transition frequency | f_T | $V_{CB} = 6V, I_E = -50mA, f = 200MHz$ | | 100 | | MHz |
| Collector output capacitance | C_{ob} | $V_{CB} = 6V, I_E = 0, f = 1MHz$ | | 23 | | pF |

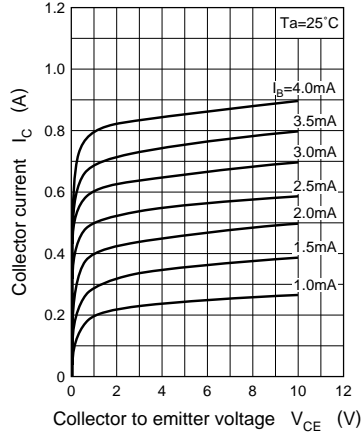


Marking symbol : 10

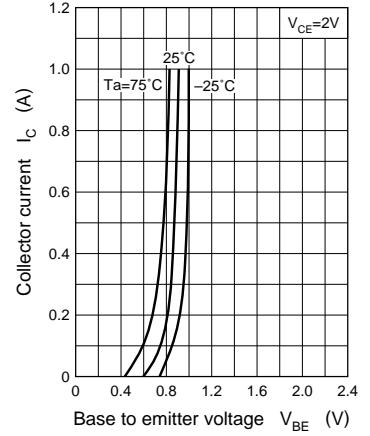
$P_C - T_a$



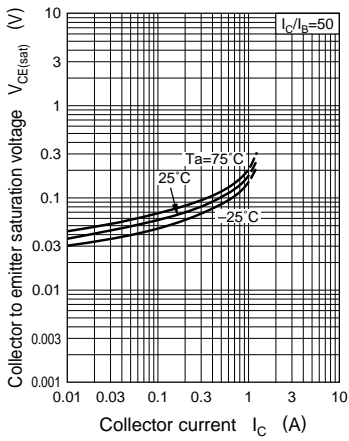
$I_C - V_{CE}$



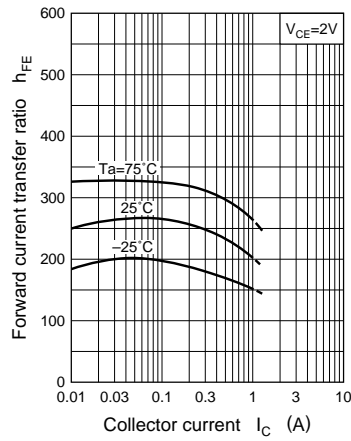
$I_C - V_{BE}$



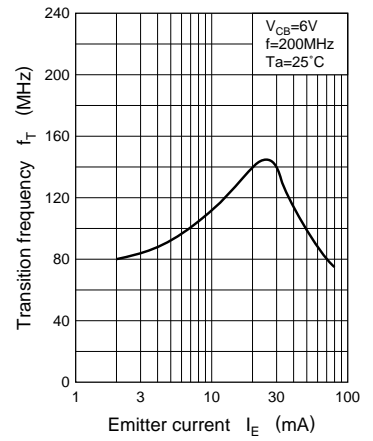
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

